**Product data sheet** 

## 1. Product profile

#### 1.1 General description

Passivated sensitive gate triac in a SOT54 plastic package

#### 1.2 Features

- Sensitive gate
- Direct interfacing to logic level ICs
- Gate triggering in four quadrants
- Direct interfacing to low power gate drive circuits

### 1.3 Applications

- General purpose switching and phase control
- Low power AC fan speed controllers

#### 1.4 Quick reference data

- $V_{DRM} \le 600 \text{ V}$
- $\blacksquare \quad I_{GT} \leq 5 \ mA$
- $I_{GT} \le 7 \text{ mA } (T2-G+)$

- $I_{T(RMS)} \le 0.8 A$
- $I_{TSM} \le 9 \text{ A (t = 20 ms)}$

## 2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	main terminal 2 (T2)		<b>.</b> .
2	gate (G)		T2—T1
3	main terminal 1 (T1)		sym051
		SOT54 (TO-92)	



Triac logic level

# 3. Ordering information

#### Table 2. Ordering information

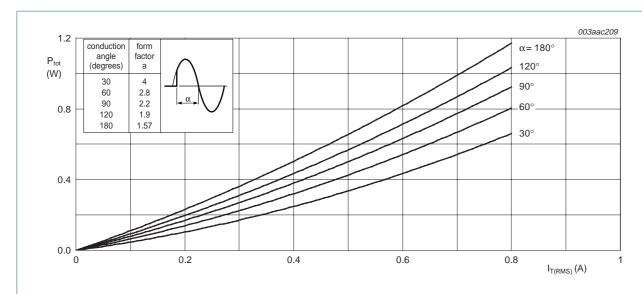
Type number	Package				
	Name	Description	Version		
Z00607MA	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54		

# 4. Limiting values

#### Table 3. Limiting values

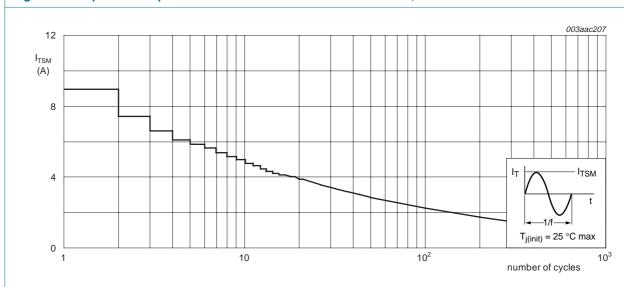
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{lead} \le 55$ °C; see Figure 4 and 5	-	0.8	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3			
		t = 20 ms	-	9	Α
		t = 16.7 ms	-	10	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	$t_p = 10 \text{ ms}$	-	0.32	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_{TM} = 1 \text{ A}; I_G = 20 \text{ mA};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$			
		T2+ G+	-	50	A/μs
		T2+ G-	-	50	A/μs
		T2- G-	-	50	A/μs
		T2- G+	-	10	A/μs
I <sub>GM</sub>	peak gate current		-	1	Α
$P_{GM}$	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	+150	°C
Tj	junction temperature		-	125	°C



 $\alpha$  = conduction angle

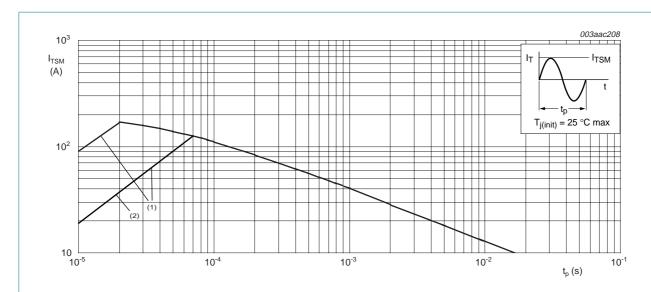
Fig 1. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

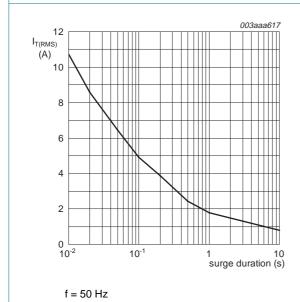
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 $t_p \le 20 \text{ ms}$ 

- (1) dI<sub>T</sub>/dt limit
- (2) T2- G+ quadrant limit

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values



 $T_{lead} = 55 \, ^{\circ}C$ 

Fig 4. RMS on-state current as a function of surge duration; maximum values

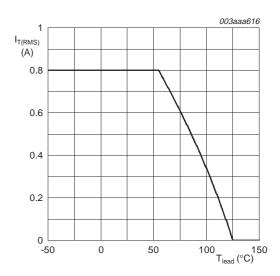


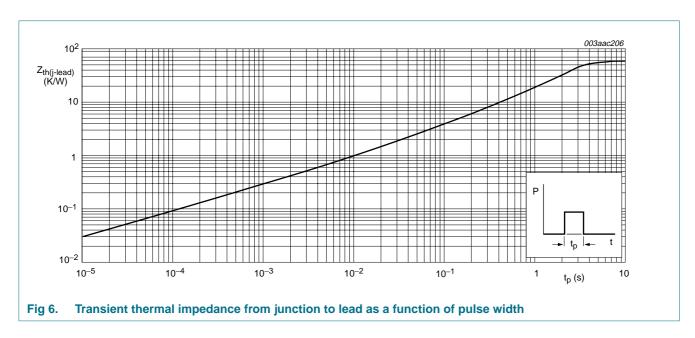
Fig 5. RMS on-state current as a function of lead temperature; maximum values

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## 5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	full cycle; see Figure 6	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	full cycle; printed circuit board mounted; lead length = 4 mm	-	150	-	K/W



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## 6. Static characteristics

Table 5. Static characteristics

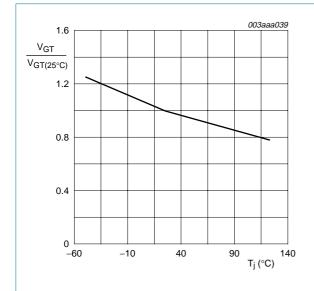
 $T_j = 25 \,^{\circ}C$  unless otherwise specified.

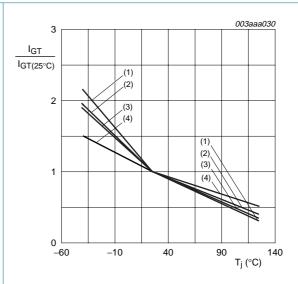
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; see } \frac{\text{Figure 8}}{}$				
		T2+ G+	-	1	5	mA
		T2+ G-	-	2	5	mA
		T2- G-	-	2	5	mA
		T2- G+	-	4	7	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 10}{\text{Figure } 10}$				
		T2+ G+	-	1	10	mA
		T2+ G-	-	5	10	mA
		T2- G-	-	1	10	mA
		T2- G+	-	2	10	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 11}{\text{Figure } 11}$	-	1	10	mA
$V_{T}$	on-state voltage	I <sub>T</sub> = 0.85 A; see <u>Figure 9</u>	-	1.35	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; see } \frac{\text{Figure 7}}{}$	-	0.9	2	V
		$V_D = V_{DRM}; I_T = 0.1 A; T_j = 110 ^{\circ}C$	0.1	0.7	-	V
I <sub>D</sub>	off-state current	$V_D = V_{DRM(max)}; T_j = 125 ^{\circ}C$	-	0.1	0.5	mA

## 7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$ ; $T_j = 110$ °C; exponential waveform; gate open circuit	30	45	-	V/μs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_{DM} = V_{DRM(max)}; T_j = 50  ^{\circ}C; I_{TM} = 0.84  A;$ $dI_{com}/dt = 0.3  A/ms$	-	5	-	V/μs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 1 \text{ A}; V_D = V_{DRM(max)}; I_G = 25 \text{ mA}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



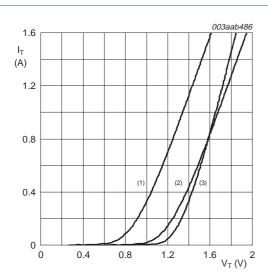


- (1) T2-G-
- (2) T2+ G-
- (3) T2+ G+
- (4) T2-G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature

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V<sub>o</sub> = 1.171 V

 $R_s = 0.5125 \Omega$ 

(1)  $T_i = 125$  °C; typical values

(2)  $T_j = 125 \,^{\circ}C$ ; maximum values

(3)  $T_j = 25$  °C; maximum values

Fig 9. On-state current as a function of on-state voltage

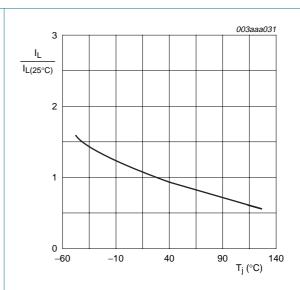


Fig 10. Normalized latching current as a function of junction temperature

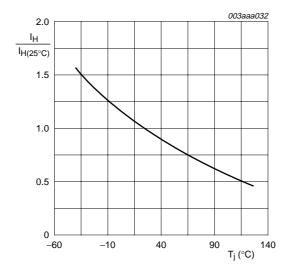


Fig 11. Normalized holding current as a function of junction temperature

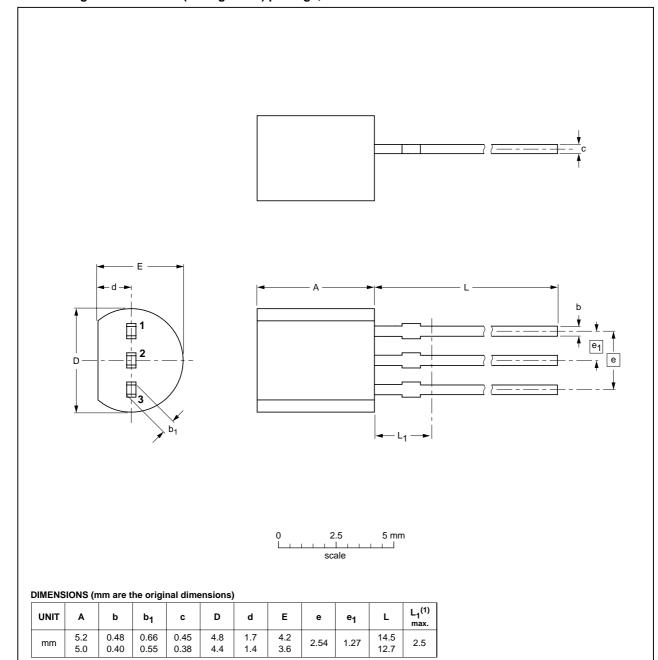
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## 8. Package outline

#### Plastic single-ended leaded (through hole) package; 3 leads

SOT54



#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A		<del>-04-06-28-</del> 04-11-16

Fig 12. Package outline SOT54 (TO-92)

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# 9. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Z00607MA_1	20080226	Product data sheet	-	-

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#### 10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# **Z00607MA**

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